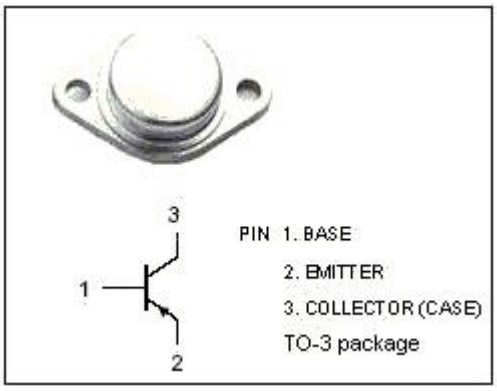
isc Silicon PNP Power Transistors 3AD53

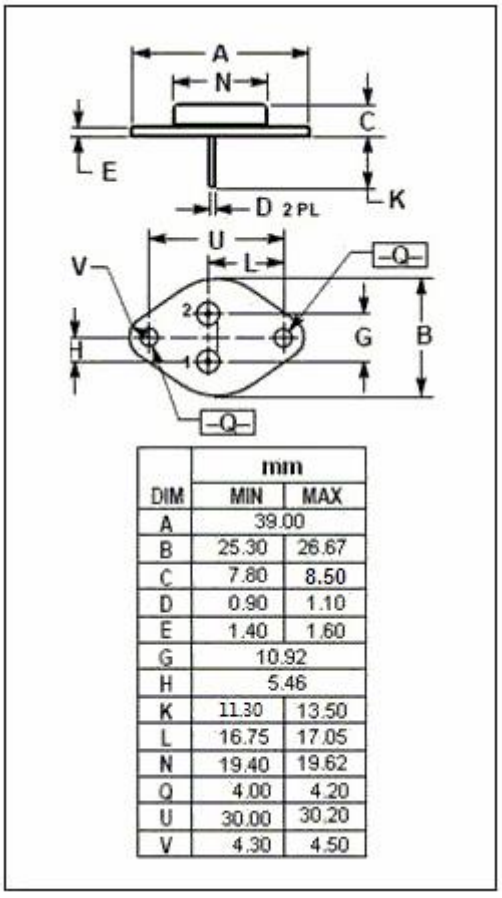
DESCRIPTION

- DC Current Gain-
  : h_{FE}=20-140@I_C= -4A
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= -1.0V(Max)@ I_C= -4A
-



APPLICATIONS

- Designed for general-purpose switching and amplifier applications



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-24	V
V_{EBO}	Emitter-Base Voltage	-20	V
I_C	Collector Current-Continuous	-6	A
P_C	Collector Power Dissipation @T_C=55℃	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.75	℃/W

isc Silicon PNP Power Transistors 3AD53

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -50mA ; I_B= 0	-24		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -0.4A		-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -4A ; V_{CE}= -4V		-1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -10V; I_B= 0		-10	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= -20V; I_E= 0		-0.5	mA
h_{FE}	DC Current Gain	I_C= -4A ; V_{CE}= -2V	20	140	
f_T	Current Gain-Bandwidth Product	I_C= -0.5A ; V_{CE}= -10V;f_{test}= 1.0MHz	10		MHz